

## 30V N-channel SGT MOSFET

### DESCRIPTION

The CX3400 uses advanced trench technology to provide excellent  $R_{D(ON)}$  and low gate charge.

This device is suitable for use as a load switch or in PWM applications.

### Product Summary

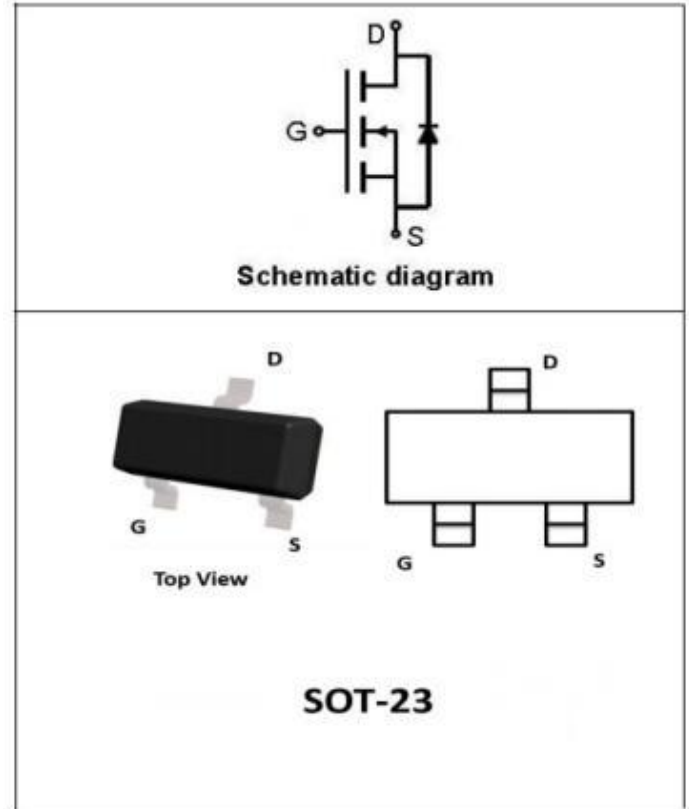
- $R_{D(ON)} < 30m\Omega$  @  $V_{GS}=10V$
- $R_{D(ON)} < 40m\Omega$  @  $V_{GS}=4.5V$

### GENERAL FEATURES

- Trench Power LV MOSFET technology
- High density cell design for low  $R_{D(ON)}$
- High Speeds switching

### Application

- Battery protection
- Load switch
- Power management



#### ■ Absolute Maximum Ratings ( $T_A=25^{\circ}C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	30	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current	$T_C=25^{\circ}C$	$I_D$	5.6	A
	$T_C=75^{\circ}C$		4.5	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	30	A
Total Power Dissipation	$T_C=25^{\circ}C$	$P_D$	1.2	W
	$T_C=70^{\circ}C$		0.9	
Thermal Resistance Junction-to-Ambient @ Steady State <sup>B</sup>		$R_{\theta JC}$	105	$^{\circ}C/W$
Junction and Storage Temperature Range		$T_J, T_{STG}$	$-55 \sim +150$	$^{\circ}C$